

IN THE CLAIMS:

The status of each claim that has been introduced in the above-referenced application is identified in the ensuing listing of the claims. This listing of the claims replaces all previously submitted claims listings.

CI 1. (Currently amended) A semiconductor device, comprising:
a semiconductor substrate including an active ~~device region~~ surface;
at least one conductive line disposed upon said active ~~device region~~ surface, said at least one conductive line being flanked by sidewall spacers;
an undoped silicon dioxide cap disposed over and in contact with said at least one conductive line;
a passivation layer over said undoped silicon dioxide cap; and
at least one contact aperture defined through said passivation layer and including at least one sidewall extending substantially perpendicularly relative to said semiconductor substrate, at least a portion of said at least one sidewall terminating at said undoped silicon dioxide cap.

2. (Original) The semiconductor device of claim 1, wherein said at least one conductive line comprises a word line.

3. (Original) The semiconductor device of claim 1, wherein said passivation layer comprises doped silicon dioxide.

4. (Original) The semiconductor device of claim 1, wherein said passivation layer comprises borophosphosilicate glass, phosphosilicate glass, or borosilicate glass.

5. (Original) The semiconductor device of claim 1, wherein said undoped silicon dioxide cap is at least partially exposed through said at least one contact aperture.

CI
Cont.

6. (Previously presented) A semiconductor device, comprising:
a semiconductor substrate;
at least one undoped silicon oxide structure; and
at least one doped silicon oxide structure over said at least one undoped silicon oxide structure
and having at least one sidewall substantially perpendicular to a plane of said
semiconductor substrate, at least a portion of said at least one sidewall terminating at said
at least one undoped silicon oxide structure.

7. (Original) The semiconductor device of claim 6, wherein said at least one sidewall
comprises a sidewall of an aperture.

8. (Previously presented) The semiconductor device of claim 6, wherein said at least
one sidewall at least partially defines an aperture through said at least one doped silicon oxide
structure.

9. (Original) The semiconductor device of claim 6, wherein said at least one doped
silicon oxide structure comprises borophosphosilicate glass, phosphosilicate glass, or borosilicate
glass.

10. (Previously presented) The semiconductor device of claim 6, wherein said at least
one undoped silicon oxide structure is at least partially located over a conductive structure.

11. (Original) The semiconductor device of claim 10, wherein said at least one
undoped silicon oxide structure comprises an insulative cap over a conductive line.

12. (Original) The semiconductor device of claim 11, wherein said insulative cap is
partially exposed through an aperture of said at least one doped silicon oxide structure defined by
said at least one sidewall.

C¹ 13. (Previously presented) The semiconductor device of claim 6, wherein said at least one undoped silicon oxide structure is at least partially exposed adjacent said at least one sidewall.
